

## **Features**

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on V<sub>F</sub>

#### **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

#### **Applications**

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



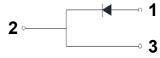
Part Number	Package	Qty(PCS)
HSCS220KGC17	TO-220H-2L	50

#### Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	v		
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1300	V		
V <sub>R</sub>	DC Peak Reverse Voltage	1200	v		
I <sub>F</sub>	Continuous Forward Current	54.5 26 20	А	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =150°C	Fig. 3
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	91 61	A	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms, Half Sine Pulse T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms, Half Sine Pulse	
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	130 110	A	$T_c=25$ °C, $t_p=10$ ms, Half Sine Pulse $T_c=110$ °C, $t_p=10$ ms, Half Sine Pulse	Fig. 8
I <sub>F,Max</sub>	Non-Repetitive Peak Forward Current	1150 950	A	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms, Pulse T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms, Pulse	Fig. 8
P <sub>tot</sub>	Power Dissipation	250 112.5	w	T <sub>c</sub> =25°C T <sub>c</sub> =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V <sub>R</sub> =0-960V	
∫i²dt	i²t value	84.5 60.5	A²s	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms	
TJ	Operating Junction Range	-55 to +175	°C		
T <sub>stg</sub>	Storage Temperature Range	-55 to +135	°C		
	TO-220 Mounting Torque	1 8.8	Nm Ibf-in	M3 Screw 6-32 Screw	









### **Electrical Characteristics**

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.5 2.2	1.8 3	V	I <sub>F</sub> = 20 A T <sub>J</sub> =25°C I <sub>F</sub> = 20 A T <sub>J</sub> =175°C	Fig. 1
I <sub>R</sub>	Reverse Current	35 65	200 400	μA	V <sub>R</sub> = 1200 V T <sub>J</sub> =25°C V <sub>R</sub> = 1200 V T <sub>J</sub> =175°C	Fig. 2
Q <sub>c</sub>	Total Capacitive Charge	99		nC	V <sub>R</sub> = 800 V, I <sub>F</sub> = 20A d <i>i</i> /d <i>t</i> = 200 A/μs T <sub>J</sub> = 25°C	Fig. 5
С	Total Capacitance	1500 93 67		pF	$V_{R} = 0 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 400 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 800 V, T_{J} = 25^{\circ}C, f = 1 MHz$	Fig. 6
E <sub>c</sub>	Capacitance Stored Energy	28		μJ	V <sub>R</sub> = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

## **Thermal Characteristics**

Symbol	mbol Parameter		Unit	Note
R <sub>ejc</sub>	Thermal Resistance from Junction to Case	0.6	°C/W	Fig. 9

# **Typical Performance**

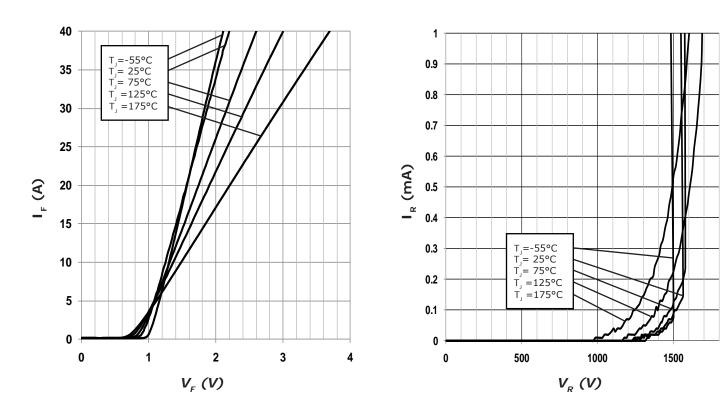
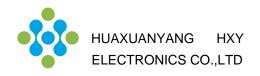


Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics



# **Typical Performance**

Q<sub>c</sub> (nc)

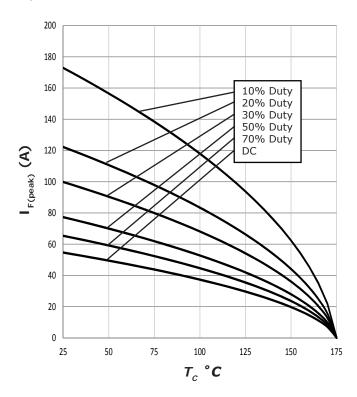
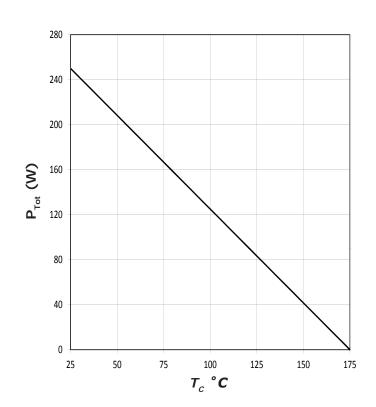
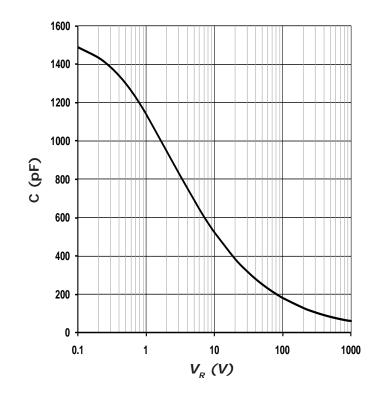


Figure 3. Current Derating



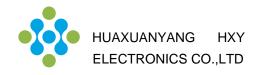




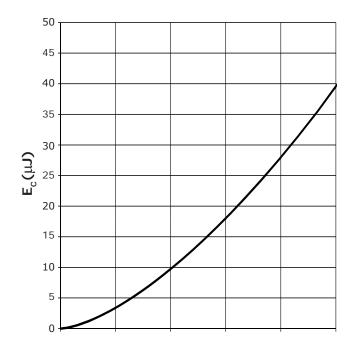


 $V_{_R}(V)$ 

Figure 6. Capacitance vs. Reverse Voltage



# **Typical Performance**



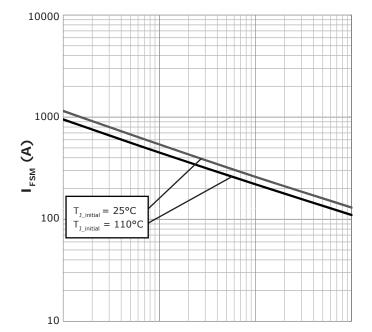


Figure 7. Typical Capacitance Stored Energy

Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

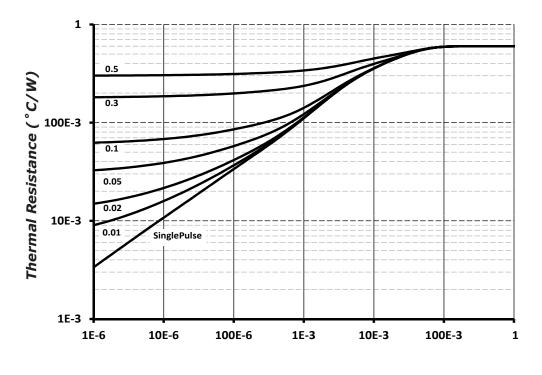
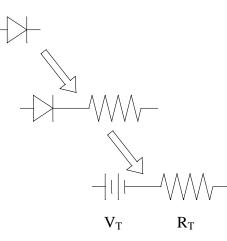


Figure 9. Transient Thermal Impedance *T (Sec)* 



### **Diode Model**

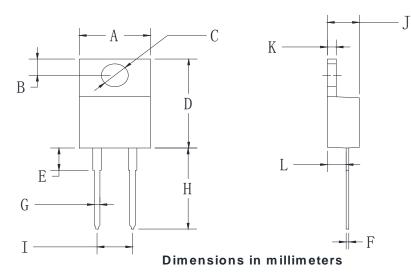


$V_{fT} = V_T + If^*R_T$
$V_{T} = 0.97 + (T_{J}^{*} - 1.40^{*}10^{-3})$ $R_{T} = 0.023 + (T_{J}^{*} 2.71^{*}10^{-4})$
Note: T, = Diode Junction Tempera

Note:  $T_j$  = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

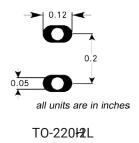


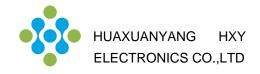
Package Information TO-220H-2L



TO-220H-2L						
Dim	Min	Max				
А	9.5	10.9				
В	2.22	3.27				
С	3.34	4.31				
D	14.5	15.5				
E	3.16	4.46				
F	0.28	0.64				
G	0.68	0.94				
Н	13.06	14.62				
I	4.55	5.60				
J	4.04	5.1				
K	1.14	1.4				
L	2.14	3.19				

**Recommended Solder Pad Layout** 





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